

产品规格书

Specifcation of products

产品名称: 三相全控桥

产品型号: MDST75A-H3

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

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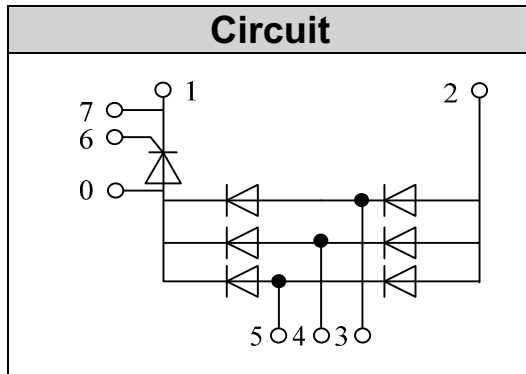
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拟制	审核	核准
林益龙	曹剑龙	宗瑞

Three Phase Bridge + Thyristor



VRRM / VDRM 800 to 1800V
IFAV / ITAV 75A

Features

- Blocking voltage:800 to 1800V
- Three Phase Bridge and a Thyristor
- Isolated Module package

Applications

- Inverter for AC or DC motor control
- Current stabilized power supply
- Switching power supply

Module Type

TYPE	VRRM /VDRM	VRSM
MDST75A800VH3	800V	900V
MDST75A1200VH3	1200V	1300V
MDST75A1600VH3	1600V	1700V
MDST75A1800VH3	1800V	1900V

◆Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
ID	Output Current(D.C.)	Tc=101℃ Three phase full wave	75	A
IFSM	Surge forward current	t=10mS Tvj =45℃	920	A
i ² t	Circuit Fusing Consideration		4200	A ² s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
Tvj	Operating Junction Temperature		-40 to +150	℃
Tstg	Storage Temperature		-40 to +125	℃
Mt	Mounting Torque	To terminals(M5)	3±5%	Nm
Ms		To heatsink(M5)	3±5%	Nm
Weight		Module (Approximately)	210	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
Rth(j-c)	Thermal Impedance, max.	Junction to Case(TOTAL)	0.20	℃/W
Rth(c-s)	Thermal Impedance, max.	Case to Heatsink	0.10	℃/W

Electrical Characteristics

Symbol	Item	Conditions	Values	Units
VFM	Forward Voltage Drop, max.	T=25℃ IF =100A	1.30	V
IRRM	Repetitive Peak Reverse Current, max.	Tvj =25℃ VRD=VRRM Tvj =150℃ VRD=VRRM	≤0.5 ≤6	mA mA

◆Thyristor

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_{TAV}	Average On-State Current	$T_c=99^{\circ}\text{C}$, Single Phase half wave 180° conduction	75	A
I_{TSM}	Surge On-State Current	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$ (50Hz), sine $V_R=0$	920	A
i^2t	Circuit Fusing Consideration		4200	A^2s
Visol	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1 min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
M_t	Mounting Torque	To terminals(M5)	$3 \pm 5\%$	Nm
M_s		To heatsink(M5)	$3 \pm 5\%$	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$, $V_D=1/2V_{DRM}$, $I_G=100\text{mA}$ $d_i/d_t=0.1\text{A}/\mu\text{s}$	150	$\text{A}/\mu\text{s}$
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$, $V_D=2/3V_{DRM}$, linear voltage rise	500	$\text{V}/\mu\text{s}$

Electrical and Thermal Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V_{TM}	Peak On-State Voltage, max.	$T=25^{\circ}\text{C}$ $I_T=100\text{A}$		1.35	V	
I_{RRM}/I_{DRM}	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	$T_{VJ}=T_{VJM}$, $V_R=V_{RRM}$, $V_D=V_{DRM}$		20	mA	
V_{GT}	Gate Trigger Voltage, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		3	V	
I_{GT}	Gate Trigger Current, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		150	mA	
Rth(j-c)	Thermal Impedance, max.	Junction to Case			0.30	$^{\circ}\text{C}/\text{W}$
Rth(c-s)	Thermal Impedance, max.	Case to Heatsink			0.10	$^{\circ}\text{C}/\text{W}$

Performance Curves

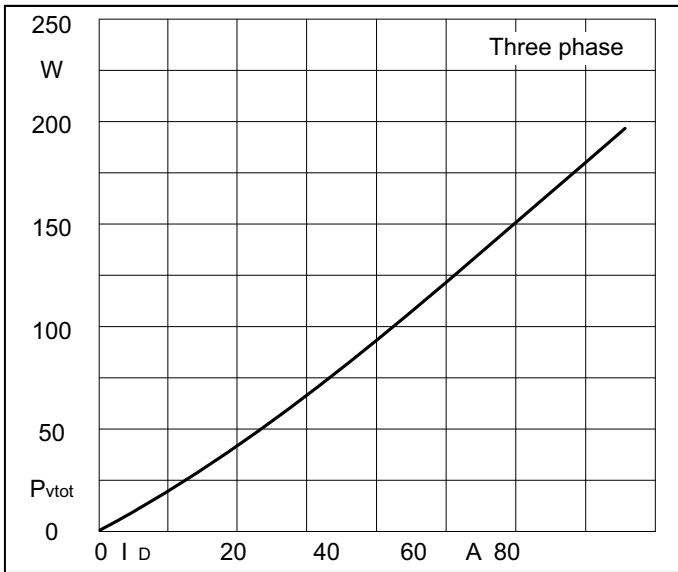


Fig1. Power dissipation

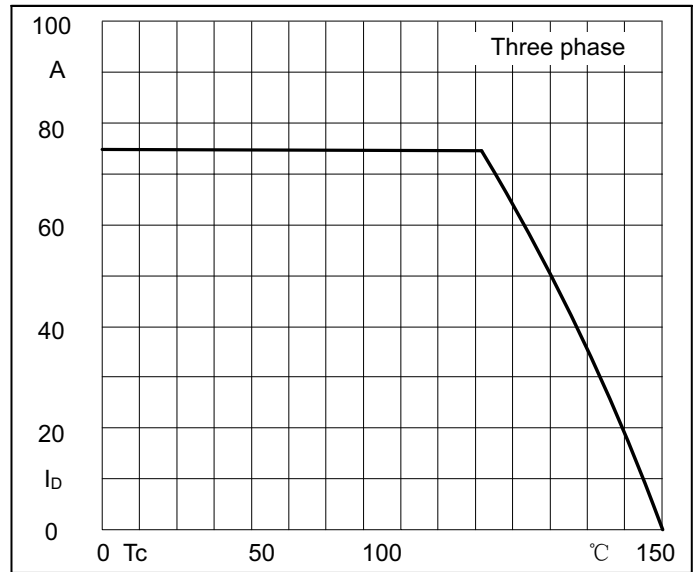


Fig2. Forward Current Derating Curve

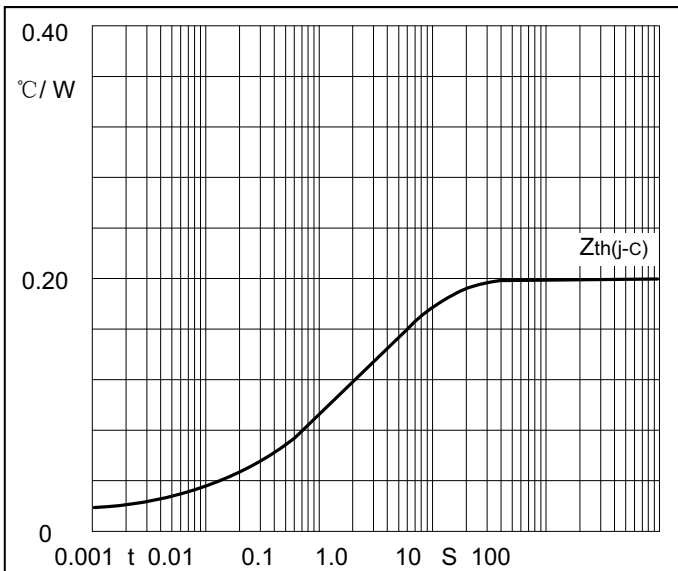


Fig3. Transient thermal impedance

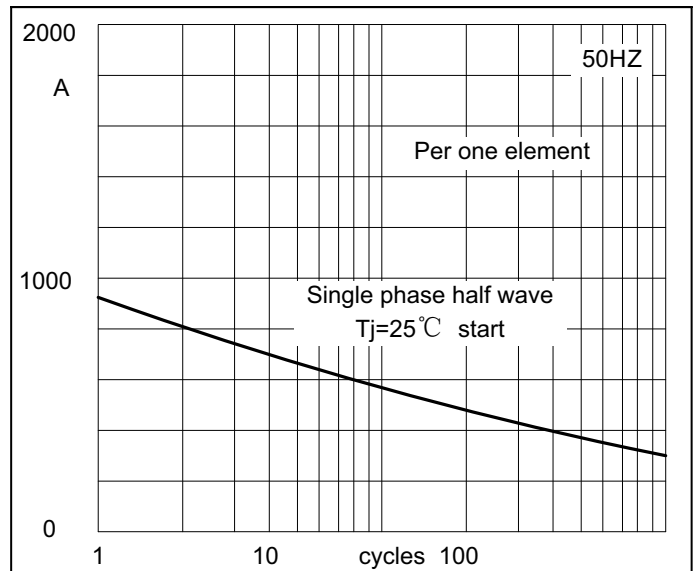


Fig4. Max Non-Repetitive Forward Surge Current

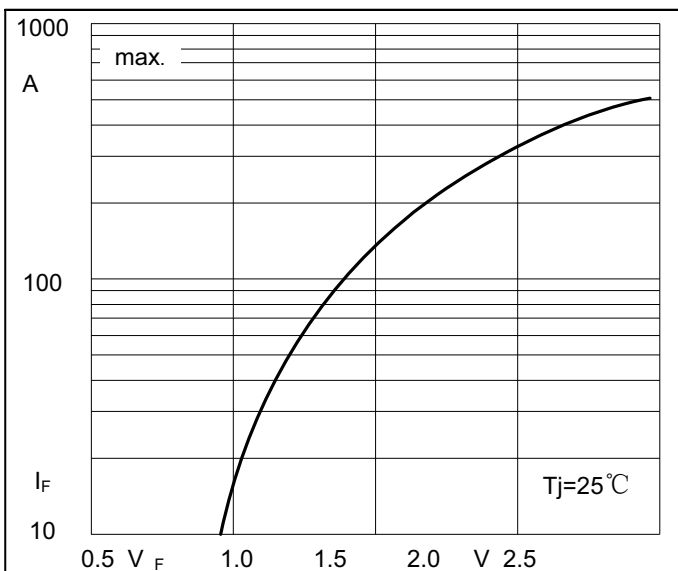


Fig5. Forward Characteristics

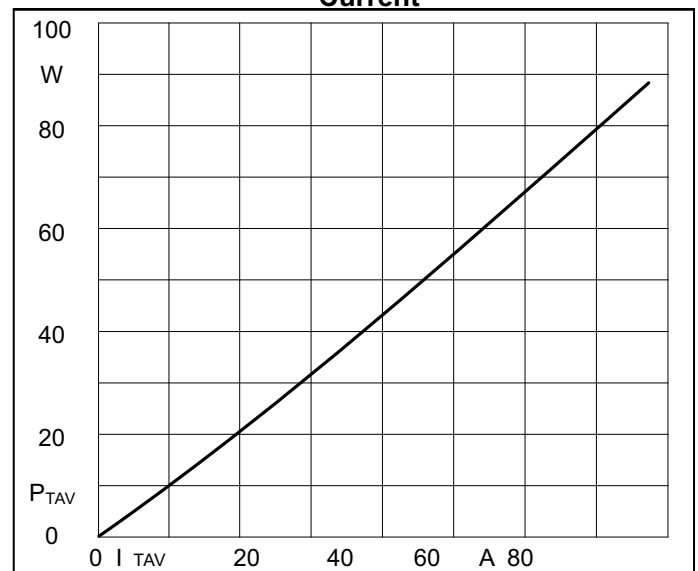


Fig6. SCR Power dissipation

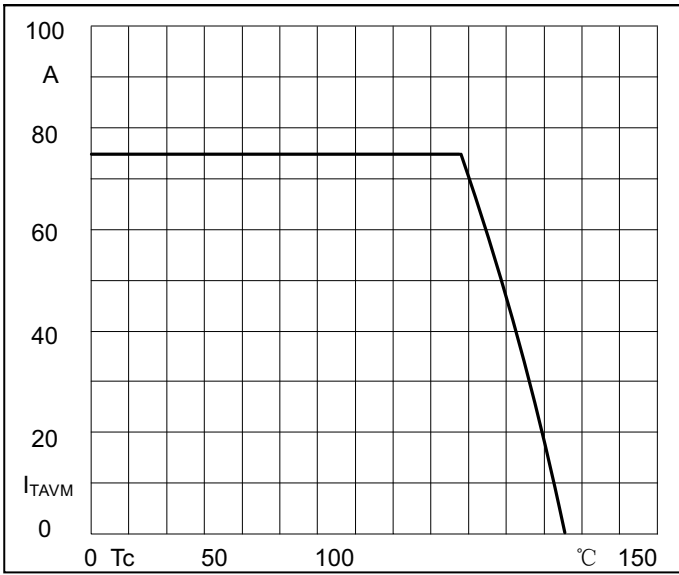


Fig7. SCR Forward Current Derating Curve

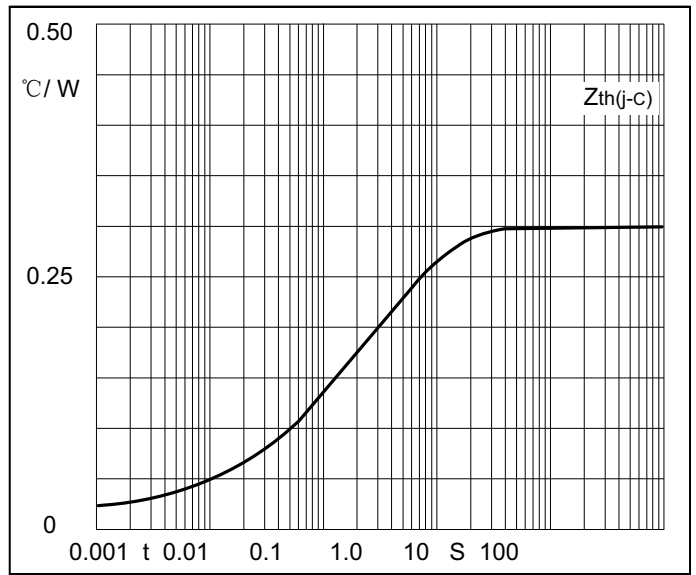


Fig8. SCR Transient thermal impedance

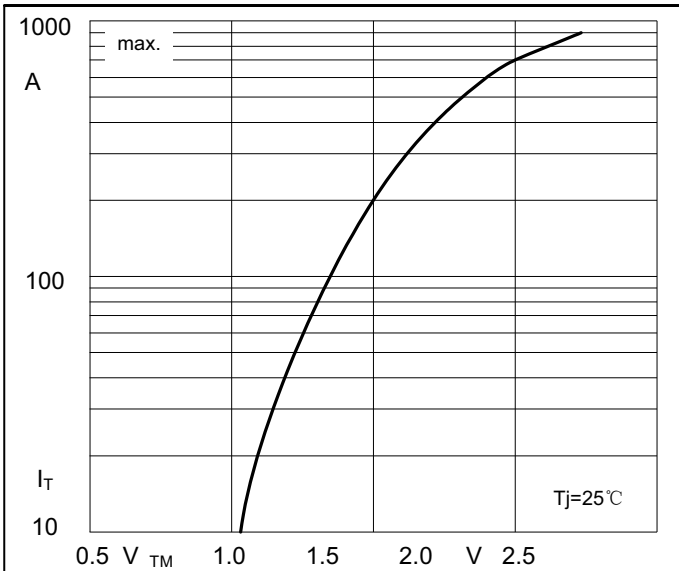


Fig9. SCR Forward Characteristics

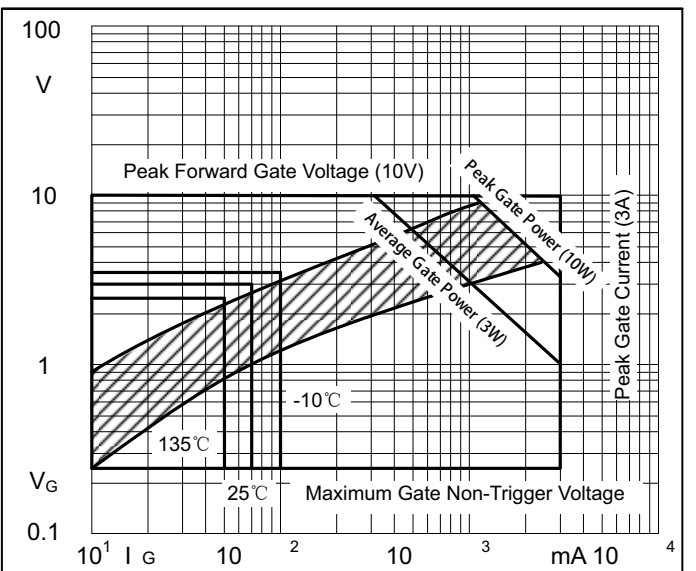
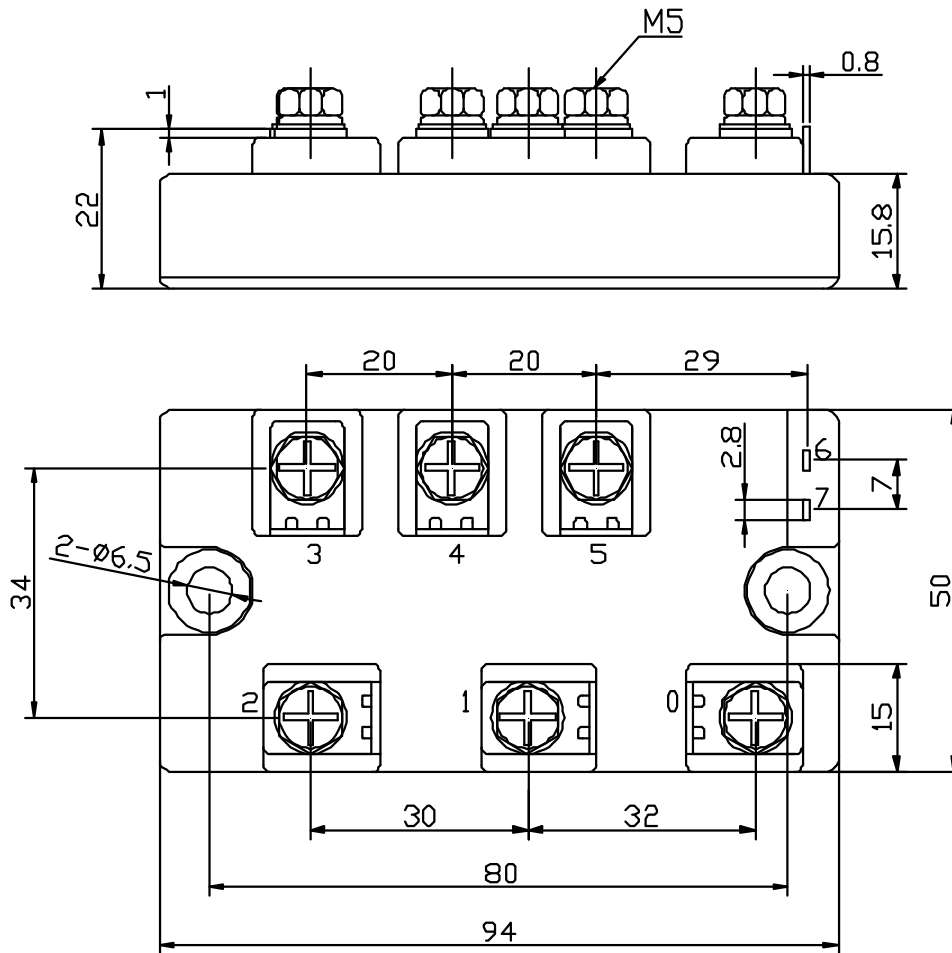


Fig10. Gate trigger Characteristics

Package Outline Information



Dimensions in mm

